

AMENDMENTS TO THE SPECIFICATION

Amend the paragraph at page 6, lines 3-14, as follows:

The inventor, however, find uniquely that formation of an AlN single crystalline layer 2 instead of the conventional low-temperature buffer layer 100 on the sapphire substrate 1, as shown in FIG. 1(b), causes the sapphire substrate 1 to be warped so as to be concave toward the ~~nitride compound semiconductor~~ AlN single crystalline layer 2, contrary to the prior-art commonsense. Based on these results, the inventor consider than when the ~~AlN~~ AlN single crystalline layer 2 is formed on the sapphire substrate 1 and a layer having a lattice constant larger than the AlN single crystalline layer 2 is formed on the AlN single crystalline layer 2, stresses would be modified and the warp would disappear.

Amend the abstract as indicated below. A clean copy of the amended abstract appears on the following page.

ABSTRACT OF THE DISCLOSURE

A nitride compound semiconductor element having improved characteristics, productivity and yield. A nitride compound semiconductor element ~~comprises~~ includes: a sapphire substrate; a first single crystalline layer of ~~AlN~~ AlN formed on said sapphire substrate; a second single crystalline layer formed on said first single crystalline layer, said second single crystalline layer being made of $Al_xGa_{1-x}N$ ($0.8 \leq x \leq 0.97$) and having a thickness of equal to or more than $0.3 \mu m$ and equal to or less than $6 \mu m$; and a device structure section of a nitride semiconductor formed on said second single crystalline layer.